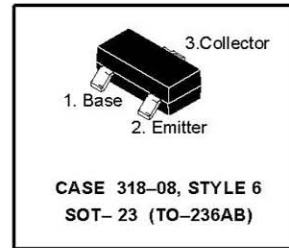
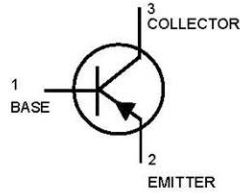


PNP Silicon



● MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CE0}	-40	Vdc
Collector–Base Voltage	V_{CB0}	-40	Vdc
Emitter–Base Voltage	V_{EB0}	-5.0	Vdc
Collector Current — Continuous	I_C	-500	mAdc

● THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Alumina Substrate (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

● ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (3) ($I_C = -1.0\text{ mAdc}, I_B = 0$)	$V_{(BR)CE0}$	-40	—	Vdc
Collector–Base Breakdown Voltage ($I_C = -0.1\text{ mAdc}, I_E = 0$)	$V_{(BR)CB0}$	-40	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = -0.1\text{ mAdc}, I_C = 0$)	$V_{(BR)EB0}$	-5.0	—	Vdc
Base Cutoff Current ($V_{CE} = -35\text{ Vdc}, V_{EB} = -0.4\text{ Vdc}$)	I_{BEV}	—	-0.1	μAdc
Collector Cutoff Current ($V_{CE} = -35\text{ Vdc}, V_{EB} = -0.4\text{ Vdc}$)	I_{CEX}	—	-0.1	μAdc

- FR-5 = 1.0 x 0.75 x 0.062 in.
- Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.
- Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$; Duty Cycle $\leq 2.0\%$.

● **ELECTRICAL CHARACTERISTICS** ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ($I_C = -0.1\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$)	h_{FE}	30	—	—
($I_C = -1.0\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$)		60	—	
($I_C = -10\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$)		100	—	
($I_C = -150\text{ mA}$, $V_{CE} = -2.0\text{ Vdc}$)(3)		180	390	
($I_C = -500\text{ mA}$, $V_{CE} = -2.0\text{ Vdc}$)(3)		20	—	
Collector–Emitter Saturation Voltage(3) ($I_C = -150\text{ mA}$, $I_B = -15\text{ mA}$)	$V_{CE(sat)}$	—	-0.4	Vdc
($I_C = -500\text{ mA}$, $I_B = -50\text{ mA}$)		—	-0.75	
Base–Emitter Saturation Voltage (3) ($I_C = -150\text{ mA}$, $I_B = -15\text{ mA}$)	$V_{BE(sat)}$	-0.75	-0.95	Vdc
($I_C = -500\text{ mA}$, $I_B = -50\text{ mA}$)		—	-1.3	

● **SMALL-SIGNAL CHARACTERISTICS**

Current–Gain — Bandwidth Product ($I_C = -20\text{ mA}$, $V_{CE} = -10\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	200	—	MHz
Collector–Base Capacitance ($V_{CB} = -10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{cb}	—	8.5	pF
Emitter–Base Capacitance ($V_{BE} = -0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{eb}	—	30	pF
Input Impedance ($V_{CE} = -10\text{ Vdc}$, $I_C = -1.0\text{ mA}$, $f = 1.0\text{ kHz}$)	h_{ie}	1.5	15	k Ω
Voltage Feedback Ratio ($V_{CE} = -10\text{ Vdc}$, $I_C = -1.0\text{ mA}$, $f = 1.0\text{ kHz}$)	h_{re}	0.1	8.0	$\times 10^{-4}$
Small–Signal Current Gain ($V_{CE} = -10\text{ Vdc}$, $I_C = -1.0\text{ mA}$, $f = 1.0\text{ kHz}$)	h_{fe}	60	500	—
Output Admittance ($V_{CE} = -10\text{ Vdc}$, $I_C = -1.0\text{ mA}$, $f = 1.0\text{ kHz}$)	h_{oe}	1.0	100	μmhos

● **SWITCHING CHARACTERISTICS**

Delay Time	$(V_{CC} = -30\text{ Vdc}$, $V_{EB} = -2.0\text{ Vdc}$, $I_C = -150\text{ mA}$, $I_{B1} = -15\text{ mA}$)	t_d	—	15	ns
Rise Time		t_r	—	20	
Storage Time	$(V_{CC} = -30\text{ Vdc}$, $I_C = -150\text{ mA}$, $I_{B1} = I_{B2} = -15\text{ mA}$)	t_s	—	225	ns
Fall Time		t_f	—	30	

3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$; Duty Cycle $\leq 2.0\%$.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

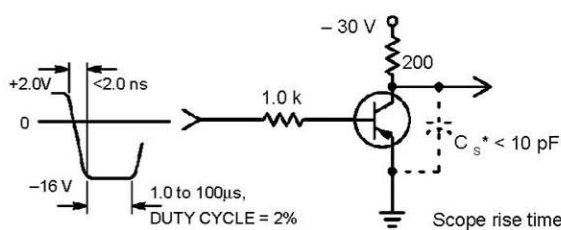


Figure 1. Turn–On Time

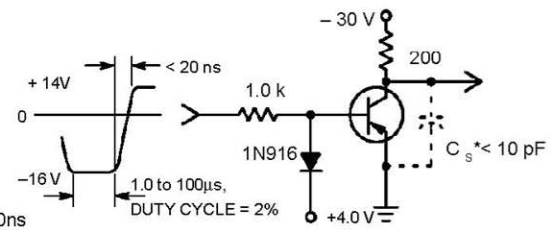
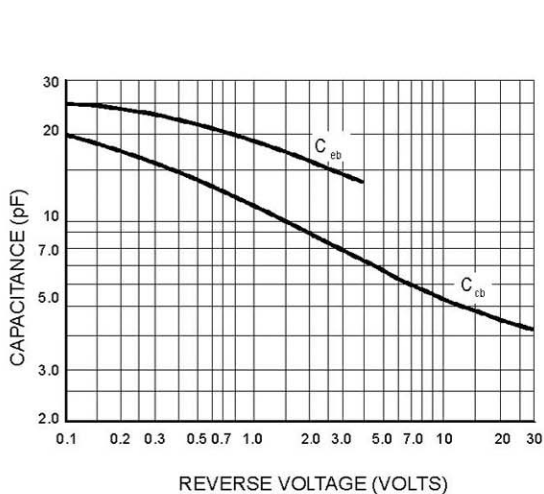


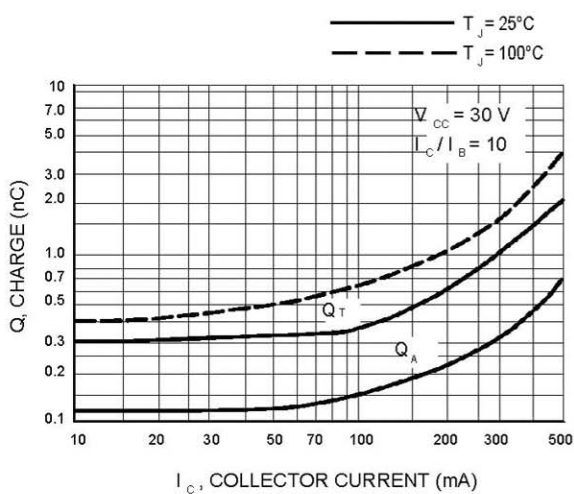
Figure 2. Turn–Off Time

TYPICAL TRANSIENT CHARACTERISTICS



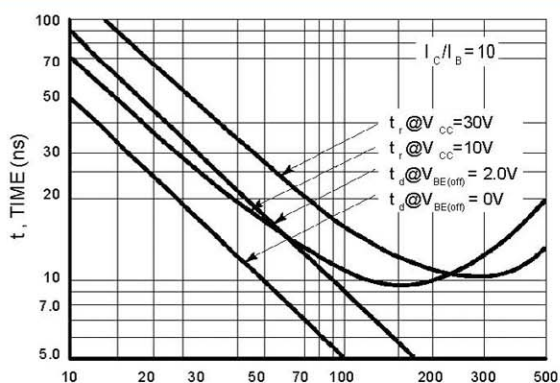
REVERSE VOLTAGE (VOLTS)

Figure 3. Capacitance



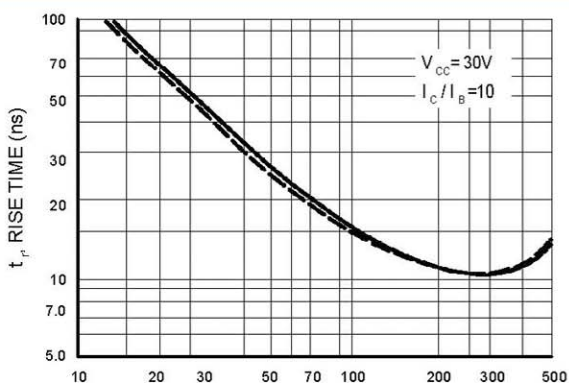
I_C , COLLECTOR CURRENT (mA)

Figure 4. Charge Data



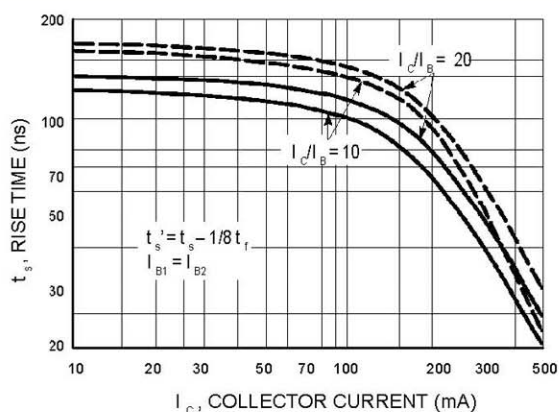
I_C , COLLECTOR CURRENT (mA)

Figure 5. Turn-On Time



I_C , COLLECTOR CURRENT (mA)

Figure 6. Rise Time



I_C , COLLECTOR CURRENT (mA)

Figure 7. Storage Time

SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

$V_{CE} = -10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$
Bandwidth = 1.0 Hz

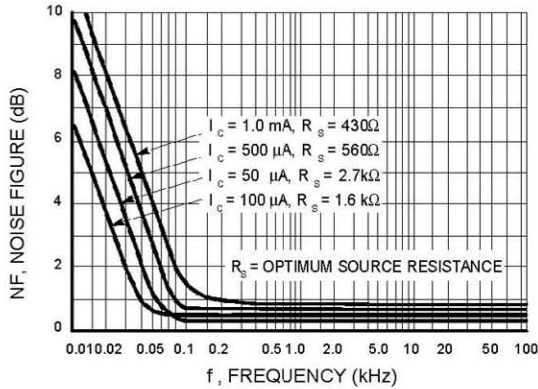


Figure 8. Frequency Effects

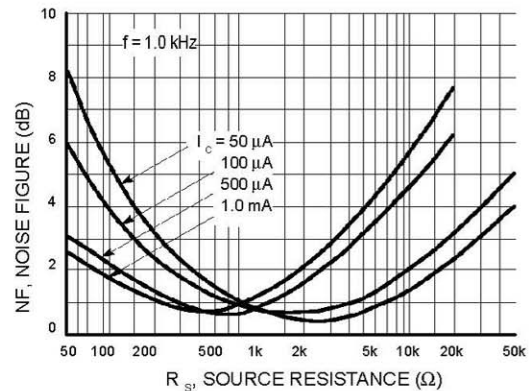


Figure 9. Source Resistance Effects

h PARAMETERS

$(V_{CE} = -10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$, $T_A = 25^\circ\text{C}$)

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from the MMBT4403LT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

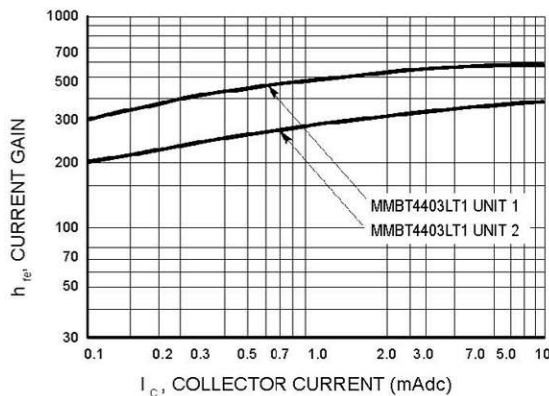


Figure 10. Current Gain

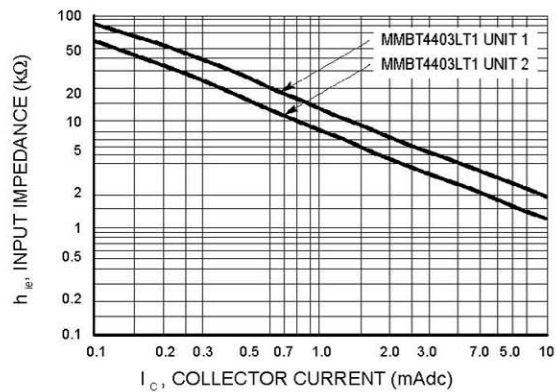


Figure 11. Input Impedance

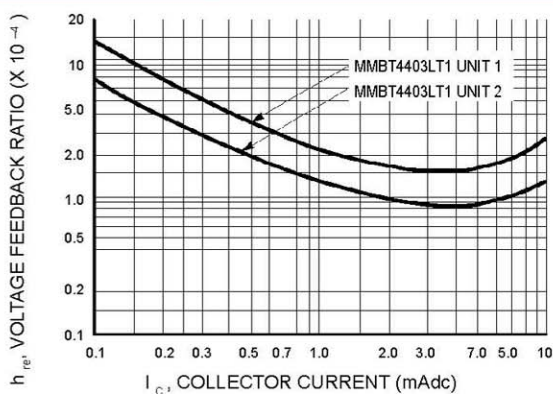


Figure 12. Voltage Feedback Ratio

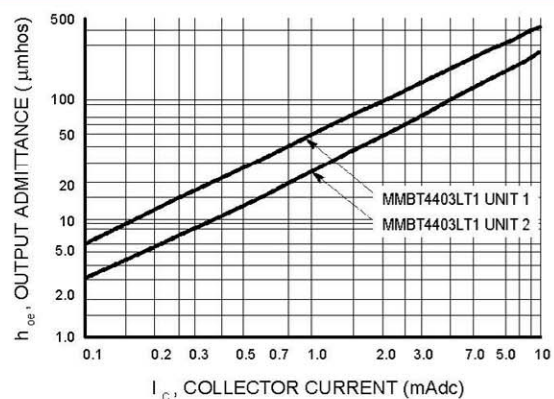


Figure 13. Output Admittance

STATIC CHARACTERISTICS

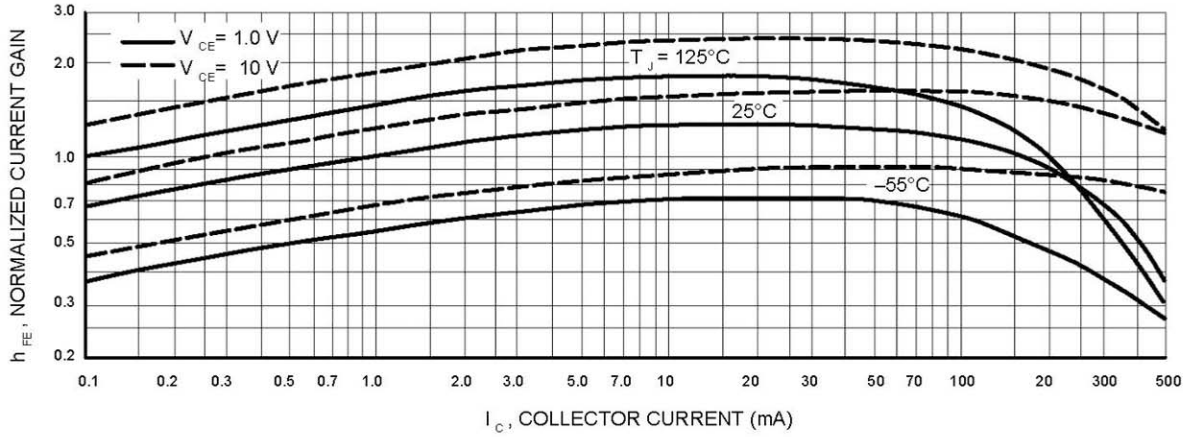


Figure 14. DC Current Gain

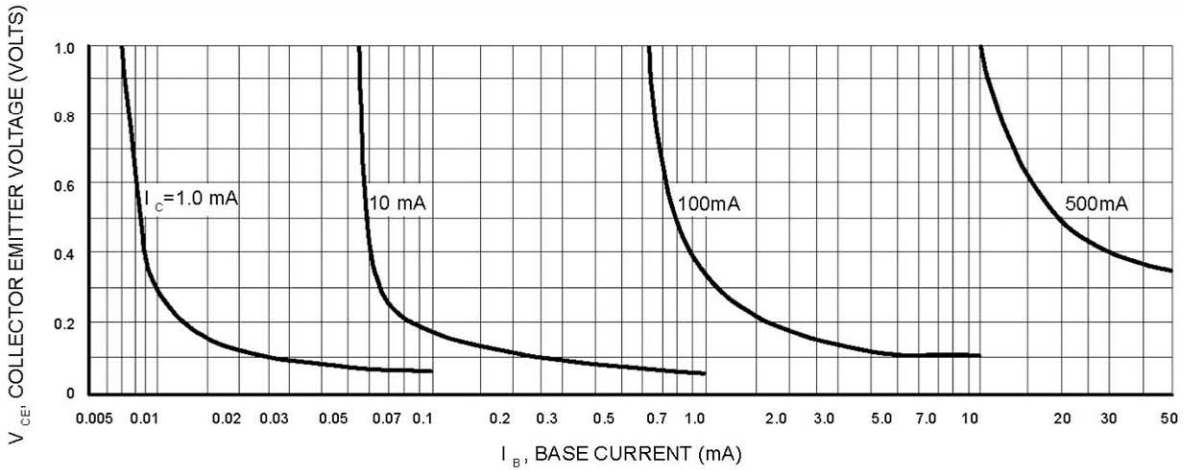


Figure 15. Collector Saturation Region

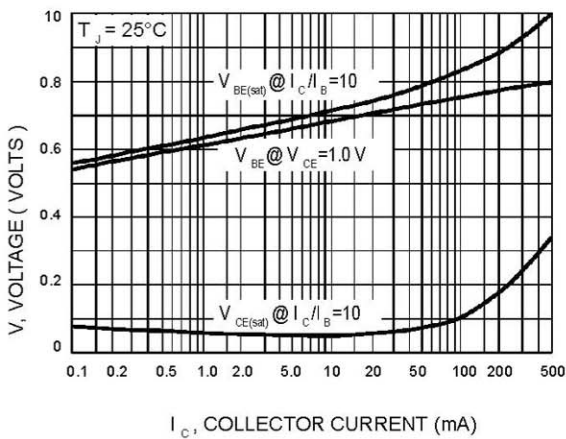


Figure 16. "On" Voltages

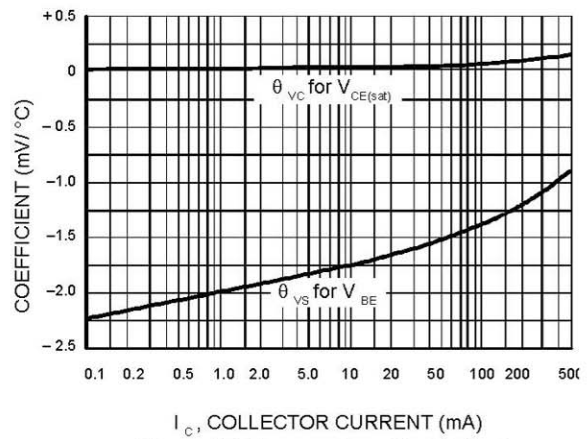


Figure 17. Temperature Coefficients